

ABSTRACT OF THE DISCLOSURE

To provide a TFT fabrication method capable of forming on a large-surface area substrate with uniform film thickness and at high film formation speed, while being a low-temperature process, a high-quality gate insulation film having good charge behavior by forming a silicon oxide film by a thin film transistor fabrication method having a channel region connected to a source region and a drain region, and a gate electrode abutting against the channel region through a gate insulation film, wherein the formation process of said gate insulation film using tetraethoxysilane as the feed gas to provide the silicon, and using plasma chemical vapor deposition under the condition that the interelectrode distance for generating the plasma is about 15mm or less.